

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

WEST[Generate Collection](#)**Search Results - Record(s) 1 through 4 of 4 returned.** **1. Document ID: US 5861135 A**

L6: Entry 1 of 4

File: USPT

Jan 19, 1999

US-PAT-NO: 5861135

DOCUMENT-IDENTIFIER: US 5861135 A

TITLE: Highly crystalline diamond

DATE-ISSUED: January 19, 1999

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 423/446[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KOMC](#) | [Drawn Desc](#) | [Image](#) **2. Document ID: US 5776552 A**

L6: Entry 2 of 4

File: USPT

Jul 7, 1998

US-PAT-NO: 5776552

DOCUMENT-IDENTIFIER: US 5776552 A

TITLE: Process for the vapor phase synthesis of diamond and highly crystalline diamond

DATE-ISSUED: July 7, 1998

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 427/577; 117/104, 423/446[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KOMC](#) | [Drawn Desc](#) | [Image](#) **3. Document ID: US 5646924 A**

L6: Entry 3 of 4

File: USPT

Jul 8, 1997

US-PAT-NO: 5646924

DOCUMENT-IDENTIFIER: US 5646924 A

TITLE: Recording and simultaneous verifying method of phase-changing type of information recording medium

DATE-ISSUED: July 8, 1997

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Nonoyama; Osamu	Yokohama	N/A	N/A	JPX
Ide; Yukio	Mishima	N/A	N/A	JPX
Harigaya; Makoto	Hiratsuka	N/A	N/A	JPX
Kageyama; Yoshiyuki	Yokohama	N/A	N/A	JPX
Deguchi; Hiroshi	Yokohama	N/A	N/A	JPX
Yamada; Katsuyuki	Mishima	N/A	N/A	JPX
Takahashi; Masaetsu	Yokohama	N/A	N/A	JPX
Iwasaki; Hiroko	Tokyo	N/A	N/A	JPX

US-CL-CURRENT: 369/53.36; 369/116, 369/275.1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMMC	Drawn Desc	Image
----------------------	-----------------------	--------------------------	-----------------------	------------------------	--------------------------------	----------------------	---------------------------	------------------------	----------------------	----------------------------	-----------------------

 4. Document ID: US 5270263 A

L6: Entry 4 of 4

File: USPT

Dec 14, 1993

US-PAT-NO: 5270263

DOCUMENT-IDENTIFIER: US 5270263 A

TITLE: Process for depositing aluminum nitride (AlN) using nitrogen plasma sputtering

DATE-ISSUED: December 14, 1993

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kim; Sung C.	Boise	ID	N/A	N/A
Yu; Chris C.	Boise	ID	N/A	N/A
Doan; Trung T.	Boise	ID	N/A	N/A

US-CL-CURRENT: 438/702; 204/192.22, 204/192.25, 438/717, 438/740, 438/761

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMMC	Drawn Desc	Image
----------------------	-----------------------	--------------------------	-----------------------	------------------------	--------------------------------	----------------------	---------------------------	------------------------	----------------------	----------------------------	-----------------------

Generate Collection

Terms	Documents
((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	4

Documents, starting with Document: **Display Format:**

WEST

[Help](#)
[Logout](#)
[Interrupt](#)
[Main Menu](#)
[Search Form](#)
[Posting Counts](#)
[Show S Numbers](#)
[Edit S Numbers](#)
[Preferences](#)

Search Results -

Terms

Documents

(((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk))

0

US Patents Full-Text Database
 US Pre-Grant Publication Full-Text Database
IPCI Abstracts Database
 EPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Database:

[Refine Search:](#)

**((aluminum adj nitride) or aln) and
(thermal adj conductivity) and (w/cmk))**

[Clear](#)

Search History

Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L7</u>
USPT	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	4	<u>L6</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L5</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cmk)	0	<u>L4</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cm adj k)	0	<u>L3</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity)	656	<u>L2</u>
PGPB	semiconductor	0	<u>L1</u>

WEST[Help](#)[Logout](#)[Interrupt](#)[Main Menu](#)[Search Form](#)[Posting Counts](#)[Show S Numbers](#)[Edit S Numbers](#)[Preferences](#)**Search Results -****Terms****Documents**

((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor

57

Database:

US Patents Full-Text Database
 US Pre-Grant Publication Full-Text Database
 JPO Abstracts Database
 EPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

[Refine Search:](#)

((aluminum adj nitride) or aln) and
 (carbon or c or oxygen or o or oxide or
 carbide) and glass and substrate and

[Clear](#)**Search History**

Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<u>L5</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<u>L4</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<u>L3</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<u>L2</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<u>L1</u>

WEST

[Help](#) [Logout](#) [Interrupt](#)

[Main Menu](#) [Search Form](#) [Posting Counts](#) [Show S Numbers](#) [Edit S Numbers](#) [Preferences](#)

Search Results -

[Terms](#) [Documents](#)

(alnc or alcн or (al adj c adj n) or (al adj n adj c))

26

Database: [US Patents Full-Text Database](#)
[US Pre-Grant Publication Full-Text Database](#)
[JPO Abstracts Database](#)
[EPO Abstracts Database](#)
[Derwent World Patents Index](#)
[IBM Technical Disclosure Bulletins](#)

[Refine Search:](#)

(alnc or alcн or (al adj c adj n) or (al adj n adj c))

[Clear](#)

Search History

Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	(alnc or alc _n or (al adj c adj n) or (al adj n adj c))	26	<u>L14</u>
JPAB	(alnc or alc _n or (al adj c adj n) or (al adj n adj c)) and glass and substrate	0	<u>L13</u>
JPAB	((aluminum adj (carb\$ or \$nitride)) or alnc or alc _n or (al adj c adj n) or (al adj n adj c)) and glass and substrate and semiconductor	32	<u>L12</u>
JPAB	((aluminum adj (carb\$ or \$nitride)) or alnc or alc _n or (al adj c adj n) or (al adj n adj c)) and glass and substrate	118	<u>L11</u>
JPAB	((aluminum adj oxynitride) or alno or alon or (al adj o adj n) or (al adj n adj o)) and glass and substrate	9	<u>L10</u>
JPAB	((aluminum adj oxynitride) or alno or alon) and glass and substrate	2	<u>L9</u>
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate and semiconductor	75	<u>L8</u>
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate	75	<u>L7</u>
JPAB	(aluminum adj oxynitride) or alno or alon	131	<u>L6</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<u>L5</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<u>L4</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<u>L3</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<u>L2</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<u>L1</u>